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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number

~~Unknown~~ 10/789-038

Filing Date

~~Even Date Herewith~~ 02-27-04

First Named Inventor

Forbes, Leonard

Group Art Unit

~~Unknown~~ 2827

Examiner Name

Pham, Ly

Sheet 1 of 5

Attorney Docket No: 1303.024US2

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Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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EXAMINER

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06/28/05

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First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown <u>2827</u>
Examiner Name	Pham, Ly

Sheet 2 of 5

Attorney Docket No: 1303.024US2

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	Application Number	Unknown 10/789,038
	Filing Date	Even Date Herewith 02-27-04
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown 2827
	Examiner Name	Pham, Ly
Sheet 3 of 5		Attorney Docket No: 1303.024US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
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Application Number	Unknown- 10/789,038
Filing Date	Even Date Herewith 02-27-04
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown- 2827
Examiner Name	Pham, Ly

Sheet 4 of 5

Attorney Docket No: 1303.024US2

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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First Named Inventor Forbes, Leonard

Group Art Unit ~~Unknown~~ 2827

Examiner Name Pham, Ly

Sheet 5 of 5

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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

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Group Art Unit	2811 2827
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Substitute Disclosure Statement Form (PTO-1448)

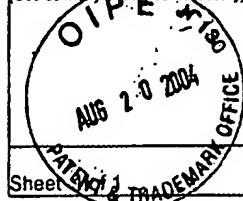
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	US-6,514,842	02/04/2003	Prall, K. D., et al.	438	593	08/08/2001
↓	US-6,730,575	05/04/2004	Eldridge, Jerome M.	257	310	08/30/2001

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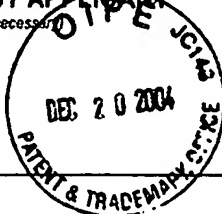
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Application Number 10/789,038
Filing Date February 27, 2004
First Named Inventor Forbes, Leonard
Group Art Unit 2811-2827
Examiner Name Pham, Ly

Sheet 1 of 1

Attorney Docket No: 1303.024US2

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Pham Ly

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Application Number	10/789,038
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Examiner Name	Pham, Ly

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